

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A cleaning method of an annealed silicon wafer consisting essentially of the steps of oxidizing a silicon wafer with ozonized water; cleaning the oxidized silicon wafer with hydrofluoric acid; and, as a final cleaning step, oxidizing the silicon wafer with ozonized water, thus obtaining a silicon wafer in which micro roughness thereof under spatial frequency of $20/\mu\text{m}$ is 0.3 to 1.5 nm^3 in terms of power spectrum density.
2. (Previously Presented) The cleaning method according to claim 1, wherein the final step of oxidizing with ozonized water takes place just after the oxidation step and the hydrofluoric acid cleaning step.
3. (Previously Presented) The cleaning method according to claim 1, wherein the concentration of the ozonized water is 10 to 60 ppm.
4. (Previously Presented) The cleaning method according to claim 1, wherein the concentration of the hydrofluoric acid is 0.5 to 2%.
5. (Previously Presented) The cleaning method according to claim 1, wherein an oxide film is present on the surface of the silicon wafer at the completion of the cleaning method.
6. (Previously Presented) A cleaning method of an annealed silicon wafer consisting essentially of the steps of oxidizing a silicon wafer with ozonized water; cleaning the oxidized silicon wafer with hydrofluoric acid; and oxidizing the silicon wafer with ozonized water, thus obtaining a silicon wafer in which micro roughness thereof under spatial frequency of $20/\mu\text{m}$ is 0.3 to 1.5 nm^3 in terms of power spectrum density.
7. (Currently Amended) The cleaning method according to claim 6, wherein further consisting essentially of the step of oxidizing with ozonized water takes place just after the oxidation step and the hydrofluoric acid cleaning step.

8. (Previously Presented) The cleaning method according to claim 6, wherein the concentration of the ozonized water is 10 to 60 ppm.
9. (Previously Presented) The cleaning method according to claim 6, wherein the concentration of the hydrofluoric acid is 0.5 to 2%.
10. (Previously Presented) The cleaning method according to claim 6, wherein an oxide film is present on the surface of the silicon wafer at the completion of the cleaning method.